

STATUS OF THE CLAIMS

The status of the claims of the present application stands as follows:

1. **(Currently amended)** A bipolar device, comprising:
  - (a) a substrate having a collector;
  - (b) an undoped epitaxial layer formed above said substrate at least above said collector;
  - (c) a doped epitaxial extrinsic base layer confronting said undoped epitaxial layer and having an aperture formed therein, said doped epitaxial layer including a remnant oxidated ring immediately surrounding said aperture;
  - (d) an emitter having a lower portion located in said aperture and confronting said undoped epitaxial layer; and
  - (e) a ~~a~~-conductor ring formed in said doped epitaxial extrinsic based layer surrounding said lower portion of said ~~base~~emitter.
2. **(Previously presented)** A bipolar device according to claim 1, further comprising a doped epitaxial intrinsic base layer located between said undoped epitaxial layer and said substrate.
3. **(Previously presented)** A bipolar device according to claim 1, wherein said emitter includes an upper portion distal from said substrate and extending over a portion of said doped epitaxial extrinsic base layer, said conductor ring extending radially out from underneath said upper portion.
4. **(Previously presented)** A bipolar device according to claim 1, wherein said conductor ring comprises a silicidated region of said doped epitaxial extrinsic base layer.
5. **(Previously presented)** A bipolar device according to claim 1, wherein said doped epitaxial extrinsic base layer has a thickness and said conductor ring has a thickness less than the thickness of said doped epitaxial extrinsic base layer.
6. **(Currently amended)** A bipolar device according to claim 1, wherein said doped epitaxial extrinsic base layer includes a remnant oxidated ring immediately surrounding said lower portion of said emitter is perfectly symmetrical about said aperture.

7. **(Currently amended)** A bipolar device, comprising:
  - (a) a substrate having a collector formed therein;
  - (b) a doped epitaxial intrinsic base layer formed on said substrate;
  - (c) an undoped epitaxial layer formed on said doped epitaxial intrinsic base layer;
  - (d) a doped epitaxial extrinsic base layer formed on said undoped epitaxial layer and including an aperture and a remnant oxidized ring immediately surrounding said aperture;
  - (e) an emitter including a lower portion and an upper portion, said lower portion being located in said aperture and said upper portion being located above said lower portion and extending over a portion of said doped epitaxial extrinsic base layer; and
  - (f) a conductor formed in said doped epitaxial extrinsic base layer and located both underneath a portion of said upper portion of said emitter and out from underneath said upper portion of said emitter.
8. **(Currently amended)** A bipolar device according to claim 7, wherein said doped epitaxial extrinsic base layer includes a remnant oxidized ring immediately surrounding said lower portion of said emitter is perfectly symmetrical about said aperture.
9. **(Currently amended)** A bipolar device according to claim 7, wherein said conductor comprises a silicidated region of said doped epitaxial extrinsic base layer.
10. **(Currently amended)** A bipolar device according to claim 7, further comprising:
  - (a) a substrate having a collector;
  - (b) an undoped epitaxial layer formed above said substrate at least above said collector;
  - (c) a doped epitaxial extrinsic base layer confronting said undoped epitaxial layer and having an aperture formed therein;
  - (d) an emitter having a lower portion located in said aperture and confronting said undoped epitaxial layer;
  - (e) a conductor ring formed in said doped epitaxial extrinsic based layer surrounding said lower portion of said emitter; and
  - (f) an emitter trench etch landing pad remnant located on said doped epitaxial extrinsic base layer immediately surrounding said aperture.

11. (Previously presented) A bipolar device according to claim 10, further comprising a nitride spacer located on top of said landing pad remnant.

Claims 12-20: (Cancelled)

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